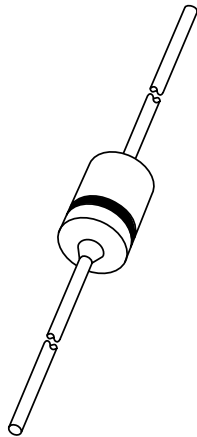


DATA SHEET



BZX79 series Voltage regulator diodes

Product specification
Supersedes data of 1996 Apr 26

1999 May 25

Voltage regulator diodes

BZX79 series

FEATURES

- Total power dissipation:
max. 500 mW
- Three tolerance series: $\pm 1\%$, $\pm 2\%$,
and approx. $\pm 5\%$
- Working voltage range:
nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power
dissipation: max. 40 W.

APPLICATIONS

- Low voltage stabilizers or voltage
references.

DESCRIPTION

Low-power voltage regulator diodes in hermetically sealed leaded glass SOD27 (DO-35) packages. The diodes are available in the normalized E24 $\pm 1\%$ (BZX79-A), $\pm 2\%$ (BZX79-B), and approx. $\pm 5\%$ (BZX79-C) tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V.



The diodes are type branded.

Fig.1 Simplified outline (SOD27; DO-35) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_F	continuous forward current		—	250	mA
I_{ZSM}	non-repetitive peak reverse current	$t_p = 100 \mu s$; square wave; $T_j = 25^\circ C$ prior to surge	see Tables 1, 2, 3 and 4		
P_{tot}	total power dissipation	$T_{amb} = 50^\circ C$; note 1	—	400	mW
		$T_{amb} = 50^\circ C$; note 2	—	500	mW
P_{ZSM}	non-repetitive peak reverse power dissipation	$t_p = 100 \mu s$; square wave; $T_j = 25^\circ C$ prior to surge; see Fig.3	—	40	W
T_{stg}	storage temperature		−65	+200	$^\circ C$
T_j	junction temperature		−65	+200	$^\circ C$

Notes

1. Device mounted on a printed circuit-board without metallization pad; lead length max.
2. Tie-point temperature $\leq 50^\circ C$; max. lead length 8 mm.

Voltage regulator diodes

BZX79 series

ELECTRICAL CHARACTERISTICS

Total BZX79-A, B and C series

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	$I_F = 10\text{ mA}$; see Fig.4	0.9	V
I_R	reverse current			
	BZX79-A/B/C2V4	$V_R = 1\text{ V}$	50	μA
	BZX79-A/B/C2V7	$V_R = 1\text{ V}$	20	μA
	BZX79-A/B/C3V0	$V_R = 1\text{ V}$	10	μA
	BZX79-A/B/C3V3	$V_R = 1\text{ V}$	5	μA
	BZX79-A/B/C3V6	$V_R = 1\text{ V}$	5	μA
	BZX79-A/B/C3V9	$V_R = 1\text{ V}$	3	μA
	BZX79-A/B/C4V3	$V_R = 1\text{ V}$	3	μA
	BZX79-A/B/C4V7	$V_R = 2\text{ V}$	3	μA
	BZX79-A/B/C5V1	$V_R = 2\text{ V}$	2	μA
	BZX79-A/B/C5V6	$V_R = 2\text{ V}$	1	μA
	BZX79-A/B/C6V2	$V_R = 4\text{ V}$	3	μA
	BZX79-A/B/C6V8	$V_R = 4\text{ V}$	2	μA
	BZX79-A/B/C7V5	$V_R = 5\text{ V}$	1	μA
	BZX79-A/B/C8V2	$V_R = 5\text{ V}$	700	nA
	BZX79-A/B/C9V1	$V_R = 6\text{ V}$	500	nA
	BZX79-A/B/C10	$V_R = 7\text{ V}$	200	nA
	BZX79-A/B/C11	$V_R = 8\text{ V}$	100	nA
	BZX79-A/B/C12	$V_R = 8\text{ V}$	100	nA
	BZX79-A/B/C13	$V_R = 8\text{ V}$	100	nA
	BZX79-A/B/C15 to 75	$V_R = 0.7V_{Znom}$	50	nA

Voltage regulator diodes

BZX79 series

Table 1 Per type BZX79-A/B2V4 to A/B24 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZX79- A or B XXX	WORKING VOLTAGE V_Z (V) at $I_{Z\text{test}} = 5\text{ mA}$				DIFFERENTIAL RESISTANCE r_{dif} (Ω)				TEMP. COEFF. S_Z (mV/K) at $I_{Z\text{test}} = 5\text{ mA}$ (see Figs 5 and 6)			DIODE CAP. C_d (pF) at $f = 1\text{ MHz}$; $V_R = 0\text{ V}$	NON-REPETITIVE PEAK REVERSE CURRENT I_{ZSM} (A) at $t_p = 100\text{ }\mu\text{s}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$
	Tol. $\pm 1\%$ (A)		Tol. $\pm 2\%$ (B)		at $I_{Z\text{test}} = 1\text{ mA}$		at $I_{Z\text{test}} = 5\text{ mA}$		MIN.	TYP.	MAX.	MAX.	MAX.
	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.					
2V4	2.37	2.43	2.35	2.45	275	600	70	100	-3.5	-1.6	0	450	6.0
2V7	2.67	2.73	2.65	2.75	300	600	75	100	-3.5	-2.0	0	450	6.0
3V0	2.97	3.03	2.94	3.06	325	600	80	95	-3.5	-2.1	0	450	6.0
3V3	3.26	3.34	3.23	3.37	350	600	85	95	-3.5	-2.4	0	450	6.0
3V6	3.56	3.64	3.53	3.67	375	600	85	90	-3.5	-2.4	0	450	6.0
3V9	3.86	3.94	3.82	3.98	400	600	85	90	-3.5	-2.5	0	450	6.0
4V3	4.25	4.35	4.21	4.39	410	600	80	90	-3.5	-2.5	0	450	6.0
4V7	4.65	4.75	4.61	4.79	425	500	50	80	-3.5	-1.4	0.2	300	6.0
5V1	5.04	5.16	5.00	5.20	400	480	40	60	-2.7	-0.8	1.2	300	6.0
5V6	5.54	5.66	5.49	5.71	80	400	15	40	-2.0	1.2	2.5	300	6.0
6V2	6.13	6.27	6.08	6.32	40	150	6	10	0.4	2.3	3.7	200	6.0
6V8	6.73	6.87	6.66	6.94	30	80	6	15	1.2	3.0	4.5	200	6.0
7V5	7.42	7.58	7.35	7.65	30	80	6	15	2.5	4.0	5.3	150	4.0
8V2	8.11	8.29	8.04	8.36	40	80	6	15	3.2	4.6	6.2	150	4.0
9V1	9.00	9.20	8.92	9.28	40	100	6	15	3.8	5.5	7.0	150	3.0
10	9.90	10.10	9.80	10.20	50	150	8	20	4.5	6.4	8.0	90	3.0
11	10.89	11.11	10.80	11.20	50	150	10	20	5.4	7.4	9.0	85	2.5
12	11.88	12.12	11.80	12.20	50	150	10	25	6.0	8.4	10.0	85	2.5
13	12.87	13.13	12.70	13.30	50	170	10	30	7.0	9.4	11.0	80	2.5
15	14.85	15.15	14.70	15.30	50	200	10	30	9.2	11.4	13.0	75	2.0
16	15.84	16.16	15.70	16.30	50	200	10	40	10.4	12.4	14.0	75	1.5
18	17.82	18.18	17.60	18.40	50	225	10	45	12.4	14.4	16.0	70	1.5
20	19.80	20.20	19.60	20.40	60	225	15	55	14.4	16.4	18.0	60	1.5
22	21.78	22.22	21.60	22.40	60	250	20	55	16.4	18.4	20.0	60	1.25
24	23.76	24.24	23.50	24.50	60	250	25	70	18.4	20.4	22.0	55	1.25

Voltage regulator diodes

BZX79 series

Table 2 Per type BZX79-A/B27 to A/B75 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZX79- A or B XXX	WORKING VOLTAGE V_Z (V) at $I_{Z\text{test}} = 2\text{ mA}$				DIFFERENTIAL RESISTANCE r_{dif} (Ω)				TEMP. COEFF. S_Z (mV/K) at $I_{Z\text{test}} = 2\text{ mA}$ (see Figs 5 and 6)			DIODE CAP. C_d (pF) at $f = 1\text{ MHz}$; $V_R = 0\text{ V}$	NON-REPETITIVE PEAK REVERSE CURRENT I_{ZSM} (A) at $t_p = 100\text{ }\mu\text{s}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$
	Tol. $\pm 1\%$ (A)		Tol. $\pm 2\%$ (B)		at $I_{Z\text{test}} = 0.5\text{ mA}$		at $I_{Z\text{test}} = 2\text{ mA}$		MIN.	TYP.	MAX.	MAX.	MAX.
	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.					
27	26.73	27.27	26.50	27.50	65	300	25	80	21.4	23.4	25.3	50	1.0
30	29.70	30.30	29.40	30.60	70	300	30	80	24.4	26.6	29.4	50	1.0
33	32.67	33.33	32.30	33.70	75	325	35	80	27.4	29.7	33.4	45	0.9
36	35.64	36.36	35.30	36.70	80	350	35	90	30.4	33.0	37.4	45	0.8
39	38.61	39.39	38.20	39.80	80	350	40	130	33.4	36.4	41.2	45	0.7
43	42.57	43.43	42.10	43.90	85	375	45	150	37.6	41.2	46.6	40	0.6
47	46.53	47.47	46.10	47.90	85	375	50	170	42.0	46.1	51.8	40	0.5
51	50.49	51.51	50.00	52.00	90	400	60	180	46.6	51.0	57.2	40	0.4
56	55.44	56.56	54.90	57.10	100	425	70	200	52.2	57.0	63.8	40	0.3
62	61.38	62.62	60.80	63.20	120	450	80	215	58.8	64.4	71.6	35	0.3
68	67.32	68.68	66.60	69.40	150	475	90	240	65.6	71.7	79.8	35	0.25
75	74.25	75.75	73.50	76.50	170	500	95	255	73.4	80.2	88.6	35	0.2

Voltage regulator diodes

BZX79 series

Table 3 Per type BZX79-C2V4 to C24 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZX79 - C XXX	WORKING VOLTAGE V _Z (V) at I _{Ztest} = 5 mA		DIFFERENTIAL RESISTANCE r _{dif} (Ω)				TEMP. COEFF. S _Z (mV/K) at I _{Ztest} = 5 mA (see Figs 5 and 6)			DIODE CAP. C _d (pF) at f = 1 MHz; V _R = 0 V	NON-REPETITIVE PEAK REVERSE CURRENT I _{ZSM} (A) at t _p = 100 μs; T _{amb} = 25 °C
	Tol. approx. ±5% (C)		at I _{Ztest} = 1 mA		at I _{Ztest} = 5 mA		MIN.	TYP.	MAX.	MAX.	MAX.
	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.					
2V4	2.2	2.6	275	600	70	100	−3.5	−1.6	0	450	6.0
2V7	2.5	2.9	300	600	75	100	−3.5	−2.0	0	450	6.0
3V0	2.8	3.2	325	600	80	95	−3.5	−2.1	0	450	6.0
3V3	3.1	3.5	350	600	85	95	−3.5	−2.4	0	450	6.0
3V6	3.4	3.8	375	600	85	90	−3.5	−2.4	0	450	6.0
3V9	3.7	4.1	400	600	85	90	−3.5	−2.5	0	450	6.0
4V3	4.0	4.6	410	600	80	90	−3.5	−2.5	0	450	6.0
4V7	4.4	5.0	425	500	50	80	−3.5	−1.4	0.2	300	6.0
5V1	4.8	5.4	400	480	40	60	−2.7	−0.8	1.2	300	6.0
5V6	5.2	6.0	80	400	15	40	−2.0	1.2	2.5	300	6.0
6V2	5.8	6.6	40	150	6	10	0.4	2.3	3.7	200	6.0
6V8	6.4	7.2	30	80	6	15	1.2	3.0	4.5	200	6.0
7V5	7.0	7.9	30	80	6	15	2.5	4.0	5.3	150	4.0
8V2	7.7	8.7	40	80	6	15	3.2	4.6	6.2	150	4.0
9V1	8.5	9.6	40	100	6	15	3.8	5.5	7.0	150	3.0
10	9.4	10.6	50	150	8	20	4.5	6.4	8.0	90	3.0
11	10.4	11.6	50	150	10	20	5.4	7.4	9.0	85	2.5
12	11.4	12.7	50	150	10	25	6.0	8.4	10.0	85	2.5
13	12.4	14.1	50	170	10	30	7.0	9.4	11.0	80	2.5
15	13.8	15.6	50	200	10	30	9.2	11.4	13.0	75	2.0
16	15.3	17.1	50	200	10	40	10.4	12.4	14.0	75	1.5
18	16.8	19.1	50	225	10	45	12.4	14.4	16.0	70	1.5
20	18.8	21.2	60	225	15	55	14.4	16.4	18.0	60	1.5
22	20.8	23.3	60	250	20	55	16.4	18.4	20.0	60	1.25
24	22.8	25.6	60	250	25	70	18.4	20.4	22.0	55	1.25

Voltage regulator diodes

BZX79 series

Table 4 Per type BZX79-C27 to C75 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

BZX79 - C XXX	WORKING VOLTAGE V _Z (V) at I _{Ztest} = 2 mA		DIFFERENTIAL RESISTANCE r _{diff} (Ω)				TEMP. COEFF. S _Z (mV/K) at I _{Ztest} = 2 mA (see Figs 5 and 6)			DIODE CAP. C _d (pF) at f = 1 MHz; V _R = 0 V	NON-REPETITIVE PEAK REVERSE CURRENT I _{ZSM} (A) at t _p = 100 μs; T _{amb} = 25 °C
	Tol.approx. ±5% (C)		at I _{Ztest} = 0.5 mA		at I _{Ztest} = 2 mA						
	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.	MAX.	MAX.
27	25.1	28.9	65	300	25	80	21.4	23.4	25.3	50	1.0
30	28.0	32.0	70	300	30	80	24.4	26.6	29.4	50	1.0
33	31.0	35.0	75	325	35	80	27.4	29.7	33.4	45	0.9
36	34.0	38.0	80	350	35	90	30.4	33.0	37.4	45	0.8
39	37.0	41.0	80	350	40	130	33.4	36.4	41.2	45	0.7
43	40.0	46.0	85	375	45	150	37.6	41.2	46.6	40	0.6
47	44.0	50.0	85	375	50	170	42.0	46.1	51.8	40	0.5
51	48.0	54.0	90	400	60	180	46.6	51.0	57.2	40	0.4
56	52.0	60.0	100	425	70	200	52.2	57.0	63.8	40	0.3
62	58.0	66.0	120	450	80	215	58.8	64.4	71.6	35	0.3
68	64.0	72.0	150	475	90	240	65.6	71.7	79.8	35	0.25
75	70.0	79.0	170	500	95	255	73.4	80.2	88.6	35	0.2

Voltage regulator diodes

BZX79 series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point	lead length 8 mm.	300	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	lead length max.; see Fig.2 and note 1	380	K/W

Note

1. Device mounted on a printed circuit-board without metallization pad.

GRAPHICAL DATA

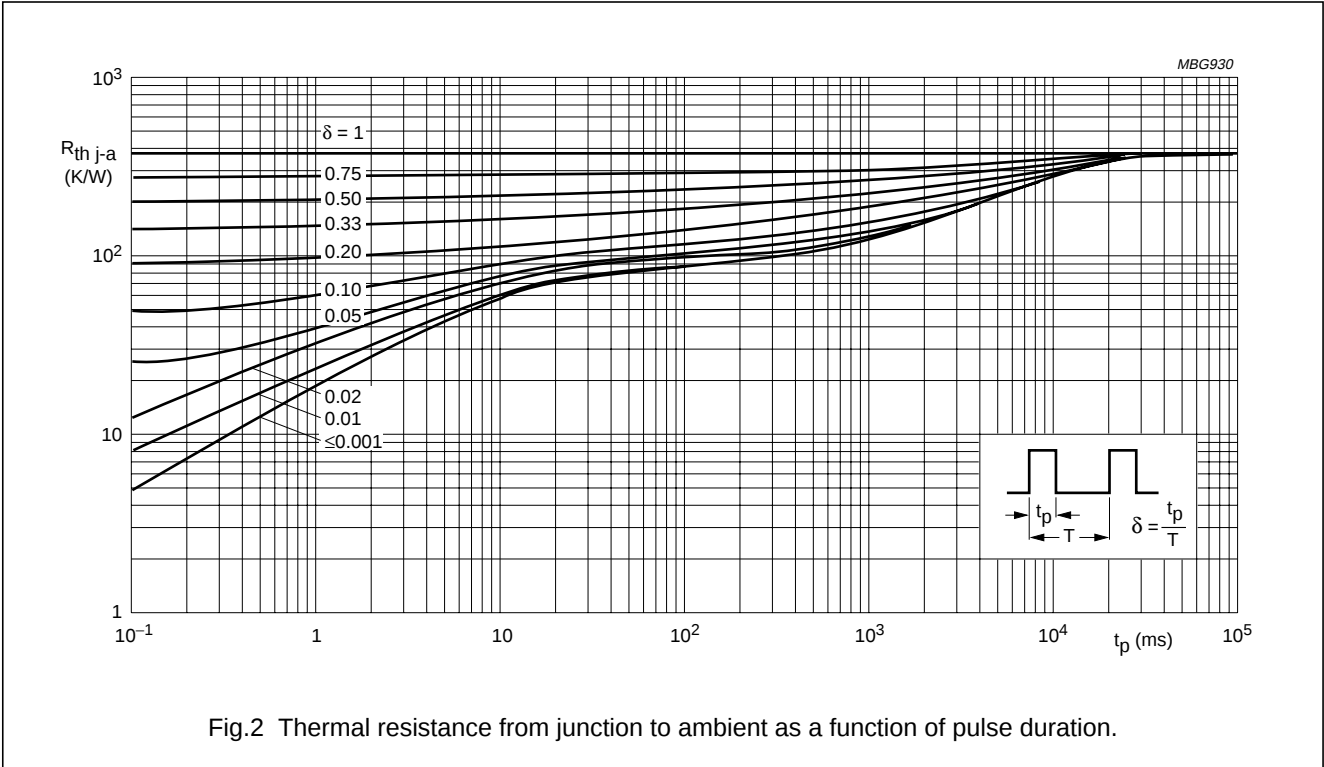
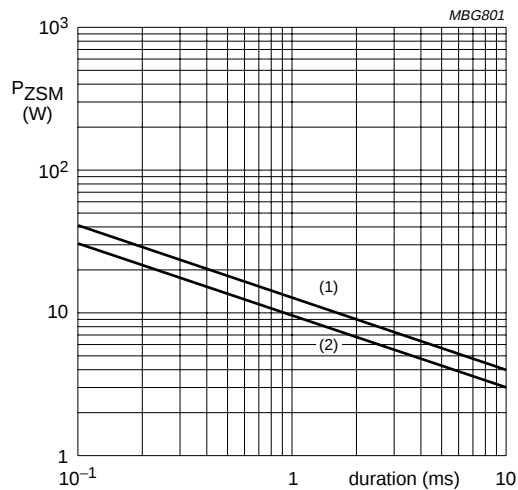


Fig.2 Thermal resistance from junction to ambient as a function of pulse duration.

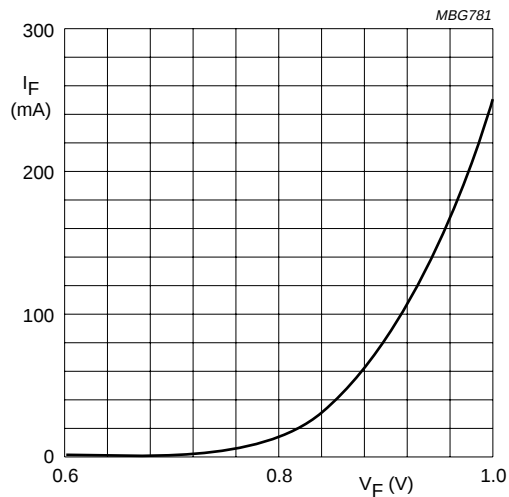
Voltage regulator diodes

BZX79 series



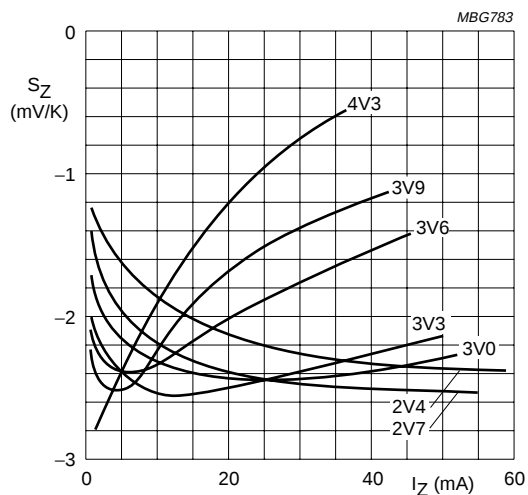
- (1) $T_j = 25\text{ }^{\circ}\text{C}$ (prior to surge).
- (2) $T_j = 150\text{ }^{\circ}\text{C}$ (prior to surge).

Fig.3 Maximum permissible non-repetitive peak reverse power dissipation versus duration.



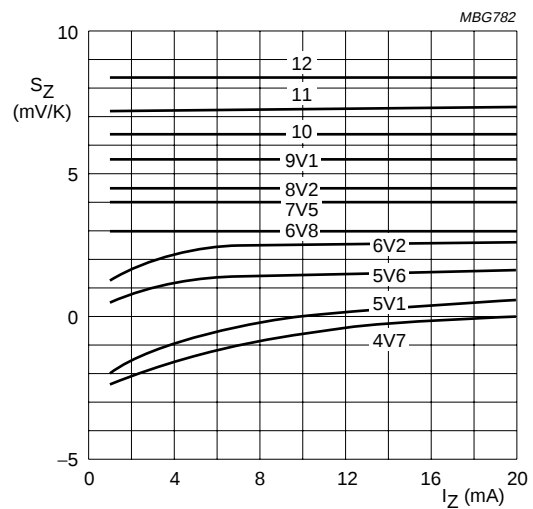
$T_j = 25\text{ }^{\circ}\text{C}$.

Fig.4 Forward current as a function of forward voltage; typical values.



BZX79-A/B/C2V4 to A/B/C4V3.
 $T_j = 25\text{ to }150\text{ }^{\circ}\text{C}$.

Fig.5 Temperature coefficient as a function of working current; typical values.



BZX79-A/B/C4V7 to A/B/C12.
 $T_j = 25\text{ to }150\text{ }^{\circ}\text{C}$.

Fig.6 Temperature coefficient as a function of working current; typical values.

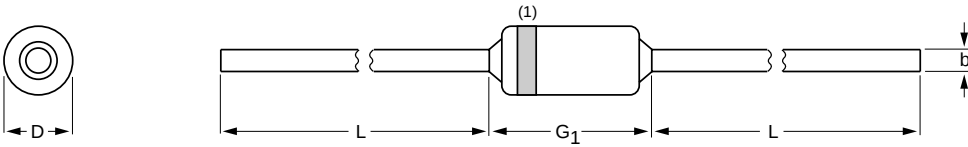
Voltage regulator diodes

BZX79 series

PACKAGE OUTLINE

Hermetically sealed glass package; axial leaded; 2 leads

SOD27

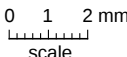


DIMENSIONS (mm are the original dimensions)

UNIT	b max.	D max.	G ₁ max.	L min.
mm	0.56	1.85	4.25	25.4

Note
1. The marking band indicates the cathode.

0 1 2 mm
scale



OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD27	A24	DO-35	SC-40			97-06-09

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

Voltage regulator diodes

BZX79 series

NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,
Tel. +45 33 29 3333, Fax. +45 33 29 3905

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 02 67 52 2531, Fax. +39 02 67 52 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,
Tel. +27 11 471 5401, Fax. +27 11 471 5398

South America: Al. Vicente Pinzon, 173, 6th floor,
04547-130 SÃO PAULO, SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 62 5344, Fax. +381 11 63 5777

For all other countries apply to: Philips Semiconductors,
International Marketing & Sales Communications, Building BE-p, P.O. Box 218,
5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

Internet: <http://www.semiconductors.philips.com>

© Philips Electronics N.V. 1999

SCA 65

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

115002/02/pp12

Date of release: 1999 May 25

Document order number: 9397 750 05894

Let's make things better.

**Philips
Semiconductors**



PHILIPS